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## BIB DATA SHEET

CONFIRMATION NO. 5339

<b>SERIAL NUMBER</b> 10/544,783	<b>FILING or 371(c) DATE</b> 08/08/2005 <b>RULE</b>	<b>CLASS</b> 117	<b>GROUP ART UNIT</b> 2812	<b>ATTORNEY DOCKET NO.</b> Q89627		
<b>APPLICANTS</b> Koichi Terashima, Tokyo, JAPAN; Yoshinao Miura, Tokyo, JAPAN; <b>** CONTINUING DATA *****</b> This application is a 371 of PCT/JP04/01315 02/09/2004 <b>** FOREIGN APPLICATIONS *****</b> JAPAN 2003-031110 02/07/2003 JAPAN 2003-129878 05/08/2003 <b>** IF REQUIRED, FOREIGN FILING LICENSE GRANTED **</b>						
Foreign Priority claimed <input checked="" type="checkbox"/> Yes <input type="checkbox"/> No 35 USC 119(a-d) conditions met <input checked="" type="checkbox"/> Yes <input type="checkbox"/> No Verified and Acknowledged <u>/PAPE A SENE/</u> Examiner's Signature		<input type="checkbox"/> Met after Allowance Initials	<b>STATE OR COUNTRY</b> JAPAN	<b>SHEETS DRAWINGS</b> 31	<b>TOTAL CLAIMS</b> 65	<b>INDEPENDENT CLAIMS</b> 9
<b>ADDRESS</b> SUGHRUE MION, PLLC 2100 PENNSYLVANIA AVENUE, N.W. SUITE 800 WASHINGTON, DC 20037 UNITED STATES						
<b>TITLE</b> Method for forming nickel silicide film, method for manufacturing semiconductor device, and method for etching nickel silicide						
<b>FILING FEE RECEIVED</b> 4350	FEES: Authority has been given in Paper No. _____ to charge/credit DEPOSIT ACCOUNT No. _____ for following:		<input type="checkbox"/> All Fees <input type="checkbox"/> 1.16 Fees (Filing) <input type="checkbox"/> 1.17 Fees (Processing Ext. of time) <input type="checkbox"/> 1.18 Fees (Issue) <input type="checkbox"/> Other _____ <input type="checkbox"/> Credit			